

In the Abstract:

Please delete the heading at page 8, line 1.

Please add a new heading at page 8, above line 2, as follows:

ABSTRACT OF THE DISCLOSURE

Please delete the paragraph at page 8, lines 2 to 3.

Please delete the paragraph at page 8, lines 4 to 8.

Please delete the paragraph at page 8, lines 9 to 14.

Please add a new paragraph at page 8, following line 14, as follows:

To form an isolation structure in a semiconductor substrate, at least two trenches are formed with a rib therebetween in the semiconductor substrate, and then the semiconductor material in the area of the trenches and particularly the rib is converted to an electrically insulating material. For example, this is accomplished by thermal oxidation of silicon semiconductor material of the rib.